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PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Application Number	Not Yet Assigned 10/777,684	
			Filing Date	Concurrently Herewith	
			First Named Inventor	Terry L. Gilton	
			Art Unit	N/A 2823	
			Examiner Name	Not Yet Assigned H. LEE	
Sheet	1	of	14	Attorney Docket Number	M4065.0699/P699-B

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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**	BB	02/21542 A1	02/2002	WIPO		
**	BC	00/48196 A1	08/2000	WIPO		

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Hein Mary Lee

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** Lee	BD	WO 97/48032	12/1997	WIPO		
** Lee	BE	WO 99/28914	06/1999	WIPO		

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** Lee	CD	Hilt, "Material Characterization of Silver Chalcogenide Programmable Metallization Cells," Dissertation, Arizona State University, May 1999.		
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<i>**Lee</i>	AL1	6,297,170	10/2001	Gabriel et al.	
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<i>**</i>	AN1	6,316,784	11/2001	Zahorik et al.	
<i>**</i>	AO1	6,329,606	12/2001	Freyman et al.	
<i>**</i>	AP1	6,348,365	02/2002	Moore et al.	
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<i>**</i>	AR1	6,376,284	04/2002	Gonzalez et al.	
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<i>**</i>	AW1	6,653,193	11/2003	Gilton	
<i>**</i>	AX1	6,638,820	10/2003	Moore	
<i>**p</i>	AU1	09/797,635	03/2001	Moore et al.	
<i>**Lee</i>	AV1	09/921,518	08/2001	Moore	

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<i>**Lee</i>	CL	Kluge, et al., "Silver Photodiffusion in Amorphous Ge _x Se _{100-x} ," 124 Journal of Non-Crystalline Solids, pp. 186-193, 1990.		

Karen Mary Lee

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			Examiner Name	Not Yet Assigned H. LEE	
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**	AX1	09/943,190	08/2001	Campbell et al.	
**	AY1	09/943,199	08/2001	Campbell et al.	
**	AZ1	09/999,883	10/2001	Moore et al.	
**	AA2	10/061,825	01/2002	Gilton et al.	
**	AB2	10/077,867	02/2002	Campbell et al.	
**	AC2	10/232,757	08/2002	Le et al.	
**	AD2	6,388,324	05/2002	Kozicki et al.	
**	AE2	5,500,532	03/1996	Kozicki et al.	
**	AF2	6,469,364	10/2002	Kozicki	
**	AG2	6,635,914	10/2003	Kozicki et al.	
** Lee	AH2	6,670,713	12/2003	Gonzalez et al.	

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**	CQ1	Belin, et al., "Ion Dynamics in the Argyrodite Compound Ag ₇ GeSe ₅ I: Non-Arrhenius Behavior and Complete Conductivity Spectra," Solid State Ionics, 143, 445-455, 2001.		
**	CR1	Benmore, et al., "Structure of Fast Ion Conducting and Semiconducting Glassy Chalcogenide Alloys," Phys. Rev. Lett., 73, 264-267, 1994.		
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** Lee	CC2	Boolchand, et al., "Onset of Rigidity in Steps in Chalcogenide Glasses," Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, pp. 97-132, 2001.		
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**	CK2	Bresser, et al., "Molecular Phase Separation and Cluster Size in GeSe ₂ Glass," Hyperfine Interactions, 27, 389-392, 1986.		
**	CL2	Cahen, et al., "Room-Temperature, Electric Field Induced Creation of Stable Devices in CuInSe ₂ Crystals," Science, 258, 271-274, 1992.		
**	CM2	Chatterjee, et al., "Current-controlled Negative-resistance Behavior and Memory Switching in Bulk As-Te-Se Glasses," J. Phys. D: Appl. Phys., 27, 2624-2627, 1994.		
**	CN2	Chen, et al., "Whisker Growth Induced by Ag Photodoping in Glassy Ge _x Se _{1-x} Films," Appl. Phys. Lett., 37, 1075-1077, 1980.		
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**	CP2	Chen, et al., "Effect of Si ₃ N ₄ on Chemical Durability of Chalcogenide Glass," J. Non-Cryst. Solids, 220, 249-253, 1997.		
**	CQ2	Cohen, et al., "A Model for an Amorphous Semiconductor Memory Device," J. Non-Cryst. Solids 8-10, 885-891, 1972.		
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** Lee	CW2	den Boer, "Threshold Switching in Hydrogenated Amorphous Silicon," Appl. Phys. Lett., 40, 812-813, 1982.		
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**	CY2	El Bouchairi, et al., "Properties of Ag _{2-x} Se _{1+x/n} -Si Diodes," Thin Solid Films, 110, 107-113, 1983.		
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**	CA3	El Ghrandi, et al., "Silver Photodissolution in Amorphous Chalcogenide Thin Films," Thin Solid Films, 218, 259-273, 1992.		
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**	CR3	Guin, et al., "Indentation Creep of Ge-Se Chalcogenide Glasses Below Tg: Elastic Recovery and Non-Newtonian Flow," J. Non-Cryst. Solids, 298, 260-269, 2002.		
**	CS3	Guin, et al., "Hardness, Toughness, and Scratchability of Germanium-selenium Chalcogenide Glasses," J. Am. Ceram. Soc., 85, 1545-52, 2002.		
**	CT3	Gupta, "On Electrical Switching and Memory Effects in Amorphous Chalcogenides," J. Non-Cryst. Sol., 3, 148-154, 1970.		
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**	CV3	Haifz, et al., "Effect of Composition on the Structure and Electrical Properties of As-Se-Cu Glasses," J. Apply. Phys., 54, 1950-1954, 1983.		
**	CW3	Hajto, et al., "Quantization Effects in Metal/a-Si:H/metal Devices," Int. J. Electronics, 73, 911-913, 1992.		
**	CX3	Hajto, et al., "DC and AC Measurements on Metal/a-Si:H/metal Room Temperature Quantised Resistance Devices," J. Non-Cryst. Solids, 266-269, 1058-1061, 2000.		
**	CY3	Hajto, et al., "Theory of Room Temperature Quantized Resistance Effects in Metal-a-Si:H-metal Thin Film Structures," J. Non-Cryst. Solids, 198-200, 825-828, 1996.		
**	CZ3	Hajto, et al., "Analogue Memory and Ballistic Electron Effects in Metal-amorphous Silicon Structures," Phil. Mag. B 63, 349-369, 1991.		
**	CA4	Hayashi, et al., "Polarized Memory Switching in Amorphous Se Film," Japan. J. Appl. Phys., 13, 1163-1164, 1974.		
**	CB4	Hegab, et al., "Memory Switching Phenomena in Thin Films of Chalcogenide Semiconductors," Vacuum, 45, 459-462, 1994.		
**	CC4	Hong, et al., "Switching Behavior in II-IV-V2 Amorphous Semiconductor Systems," J. Non-Cryst. Solids, 116, 191-200, 1990.		
**	CD4	Gosain, et al., "Nonvolatile Memory Based on Reversible Phase Transition Phenomena in Telluride Glasses," Jap. J. Appl. Phys., 28, 1013-1018, 1989.		
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**	CI4	Haifz, et al., "Effect of Composition on the Structure and Electrical Properties of As-Se-Cu Glasses," J. Apply. Phys., 54, 1950-1954, 1983.		
** Lee	CJ4	Hajto, et al., "Quantization Effects in Metal/a-Si:H/metal Devices," Int. J. Electronics, 73, 911-913, 1992.		

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** Lee	CL4	Hajto, et al., "Theory of Room Temperature Quantized Resistance Effects in Metal-a-Si:H-metal Thin Film Structures," J. Non-Cryst. Solids, 198-200, 825-828, 1996.		
** Lee	CM4	Hajto, et al., "Analogue Memory and Ballistic Electron Effects in Metal-amorphous Silicon Structures," Phil. Mag. B 63, 349-369, 1991.		
** Lee	CN4	Hayashi, et al., "Polarized Memory Switching in Amorphous Se Film," Japan. J. Appl. Phys., 13, 1163-1164, 1974.		
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** Lee	CZ4	Hajto, et al., "Analogue Memory and Ballistic Electron Effects in Metal-amorphous Silicon Structures," Phil. Mag. B 63, 349-369, 1991.		
** Lee	CA5	Hayashi, et al., "Polarized Memory Switching in Amorphous Se Film," Japan. J. Appl. Phys., 13, 1163-1164, 1974.		
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** Lee	CE5	Hu, et al., "Constant Current Forming in Cr/p+a-/Si:H/V Thin Film Devices," J. Non-Cryst. Solids, 227-230, 1187-1191, 1998.		
**	CF5	Hu, et al., "Capacitance Anomaly Near the Metal-non-metal Transition in Cr-hydrogenated Amorphous Si-V Thin-film Devices," Phil. Mag. B. 74, 37-50, 1996.		
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**	CH5	Iizima, et al., "Electrical and Thermal Properties of Semiconducting Glasses As-Te-Ge," Solid State Comm. 8, 153-155, 1970.		
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**	CK5	Jones, et al., "Switching Properties of Thin Selenium Films Under Pulsed Bias," Thin Solid Films, 40, L15-L18, 1977.		
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**	CM5	Joullie, et al., "Electrical Properties of the Amorphous Alloy As2Se5," Mat. Res. Bull., 8, 433-442, 1973.		
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**	CB6	Messoussi, et al., "Electrical Characterization of M/Se Structures (M=Ni,Bi)," Mat. Chem. And Phys., 28, 253-258, 1991.		
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**	CD6	Mitkova, et al., "Silver Incorporation in Ge-Se Glasses Used in Programmable Metallization Cell Devices," J. Non-Cryst. Solids, 299-302, 1023-1027, 2002.		
**	CE6	Miyatani, "Electronic and Ionic Conduction in (Ag _x Cu _{1-x}) ₂ Se," J. Phys. Soc. Japan, 34, 423-432, 1973.		
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**	CJ6	Nang, et al., "Electrical and Optical Parameters of GexSe _{1-x} Amorphous Thin Films," Jap. J. App. Phys., 15, 849-853, 1976.		
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**	CN6	Ovshinsky, "Reversible Electrical Switching Phenomena in Disordered Structures," Phys. Rev. Lett., 21, 1450-1453, 1968.		
**	CO6	Owen, et al., "New Amorphous-silicon Electrically Programmable Nonvolatile Switching Device," IEEE Proc., 129, 51-54, 1982.		
**	CP6	Owen, et al., "Photo-induced Structural and Physico-chemical Changes in Amorphous Chalcogenide Semiconductors," Phil. Mag. B 52, 347-362, 1985.		
** Lee	CQ6	Owen, et al., "Switching in Amorphous Devices," Int. J. Electronics, 73, 897-906, 1992.		

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Kevin Mary Lee 6/24/2005

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Substitute for form 1449A/B/PTO			Complete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Application Number	Not Yet Assigned 10/777,684
			Filing Date	Concurrently Herewith
			First Named Inventor	Terry L. Gilton
			Art Unit	N/A 2823
			Examiner Name	Not Yet Assigned H. LEE
			Attorney Docket Number	M4065.0699/P699-B
Sheet	13	of	14	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
** Lee	CR6	Pearson, et al., "Filamentary Conduction in Semiconducting Glass Diodes," App. Phys. Lett., 14, 280-282, 1969.	
**	CS6	Pinto, et al., "Electric Field Induced Memory Switching in Thin Films of the Chalcogenide System Ge-As-Se," Appl. Phys. Lett., 19, 221-223, 1971.	
**	CT6	Popescu, "The Effect of Local Non-uniformities on Thermal Switching and High Field Behavior of Structures with Chalcogenide Glasses," Solid-state Electronics, 18, 671-681, 1975.	
**	CU6	Popescu, et al., "The Contribution of the Lateral Thermal Instability to the Switching Phenomenon," J. Non-Cryst. Solids, 8-10, 531-537, 1972.	
**	CV6	Popov, et al., "Memory and Threshold Switching Effects in Amorphous Selenium," Phys. Stat. Sol. (a) 44, K71-K73, 1977.	
**	CW6	Prakash, et al., "Easily Reversible Memory Switching In Ge-As-Te Glasses," J. Phys. D: Appl. Phys., 29, 2004-2008, 1996.	
**	CX6	Rahman, et al., "Electronic Switching in Ge-Bi-Se-Te Glasses," Mat. Sci. and Eng. B12, 219-222, 1992.	
**	CY6	Ramesh, et al., "Electrical Switching in Germanium Telluride Glasses Doped With Cu and Ag," Appl. Phys. A 69, 421-425, 1999.	
**	CZ6	Rose, et al., "Amorphous Silicon Analogue Memory Devices," J. Non-Cryst. Solids, 115, 168-170, 1989.	
**	CA7	Rose, et al., "Aspects of Non-volatility in a -Si:H Memory Devices," Mat. Res. Soc. Symp. Proc. V 258, 1075-1080, 1992.	
**	CB7	Schuoocker, et al., "On the Reliability of Amorphous Chalcogenide Switching Devices," J. Non-Cryst. Solids, 29, 397-407, 1978.	
**	CC7	Sharma, et al., "Electrical Conductivity Measurements of Evaporated Selenium Films in Vacuum," Proc. Indian Natn. Sci. Acad. 46, A, 362-368, 1980.	
**	CD7	Sharma, "Structural, Electrical and Optical Properties of Silver Selenide Films," Ind. J. Of Pure and Applied Phys., 35, 424-427, 1997.	
**	CE7	Snell, et al., "Analogue Memory Effects in Metal/a-Si:H/metal Memory Devices," J. Non-Cryst. Solids, 137-138, 1257-1262, 1991.	
**	CF7	Snell, et al., "Analogue Memory Effects in Metal/a-Si:H/metal Thin Film Structures," Mat. Res. Soc. Symp. Proc. V 297, 1017-1021, 1993.	
**	CG7	Steventon, "Microfilaments in Amorphous Chalcogenide Memory Devices," J. Phys. D: Appl. Phys., 8, L120-L122, 1975.	
**	CH7	Steventon, "The Switching Mechanisms in Amorphous Chalcogenide Memory Devices," J. Non-Cryst. Solids, 21, 319-329, 1976.	
** Lee	CI7	Stocker, "Bulk and Thin Film Switching and Memory Effects in Semiconducting Chalcogenide Glasses," App. Phys. Lett., 15, 55-57, 1969.	

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Heui Ming Lee

6/9/2005

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>			Application Number	Not Yet Assigned 10/17/07, 684	
			Filing Date	Concurrently Herewith	
			First Named Inventor	Terry L. Gilton	
			Art Unit	N/A — 2823	
			Examiner Name	Not Yet Assigned H. LEE	
Sheet	14	of	14	Attorney Docket Number	M4065.0699/P699-B

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
** Lee	CJ7	Tanaka, "Ionic and Mixed Conductions in Ag Photodoping Process," Mod. Phys. Lett B 4, 1373-1377, 1990.		
**	CK7	Tanaka, et al., "Thermal Effects on Switching Phenomenon in Chalcogenide Amorphous Semiconductors," Solid State Comm., 8, 387-389, 1970.		
**	CL7	Thornburg, "Memory Switching in a Type I Amorphous Chalcogenide," J. Elect. Mat., 2, 3-15, 1973.		
**	CM7	Thornburg, "Memory Switching in Amorphous Arsenic Triselenide," J. Non-Cryst. Solids, 11, 113-120, 1972.		
**	CN7	Thornburg, et al., "Electric Field Enhanced Phase Separation and Memory Switching in Amorphous Arsenic Triselenide," Journal(?), 4609-4612, 1972.		
**	CO7	Tichy, et al., "Remark on the Glass-forming Ability in GexSe1-x and AsxSe1-x Systems," J. Non-Cryst. Solids, 261, 277-281, 2000.		
**	CP7	Titus, et al., "Electrical Switching and Short-range Order in As-Te Glasses," Phys. Rev. B 48, 14650-14652, 1993.		
**	CQ7	Tranchant, et al., "Silver Chalcogenide Glasses Ag-Ge-Se: Ionic Conduction and Exafs Structural Investigation, Transport-structure Relations in Fast Ion and Mixed Conductors," Proceedings of the 6th Riso International symposium, 9-13, September 1985.		
**	CR7	Tregouet, et al., "Silver Movements in Ag2Te Thin Films: Switching and Memory Effects," Thin Solid Films, 57, 49-54, 1979.		
**	CS7	Uemura, et al., "Thermally Induced Crystallization of Amorphous Ge0.4Se0.6," J. Non-Cryst. Solids, 117-118, 219-221, 1990.		
**	CT7	Uttech, et al., "Electric Field Induced Filament Formation in As-Te-Ge Glass," J. Non-Cryst. Solids, 2, 358-370, 1970.		
**	CU7	Viger, et al., "Anomalous Behaviour of Amorphous Selenium Films," J. Non-Cryst. Solids, 33, 267-272, 1976.		
**	CV7	Vodenicharov, et al., "Electrode-limited Currents in the Thin-film M-GeSe-M System," Mat. Chem. And Phys., 21, 447-454, 1989.		
**	CW7	Wang, et al., "High-performance Metal/silicide Antifuse," IEEE Electron Dev. Lett., 13, 471-472, 1992.		
**	CX7	Weirauch, "Threshold Switching and Thermal Filaments in Amorphous Semiconductors," App. Phys. Lett., 16, 72-73, 1970.		
**	CY7	West, et al., "Equivalent Circuit Modeling of the Ag As0.24S0.36Ag0.40 Ag System Prepared by Photodissolution of Ag," J. Electrochem. Soc., 145, 2971-2974, 1998.		
** Lee	CZ7	Zhang, et al., "Variation of Glass Transition Temperature, Tg, With Average Coordination Number, <m>, in Network Glasses: Evidence of a Threshold Behavior in the Slope [dTg/d<m>] at the Rigidity Percolation Threshold (<m>=2.4)," J. Non-Cryst. Solids, 151, 149-154, 1992.		

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Karen May Lee

6/29/2005